

IN THE SPECIFICATION:

Please replace paragraph number [0001] with the following rewritten paragraph:

[0001] This application is a divisional of application Serial No. 09/586,243, filed June 2, 2000, ~~pending~~ now U.S. Patent 6,717,245, issued April 6, 2004.

Please replace paragraph number [0023] with the following rewritten paragraph:

[0023] Semiconductor substrate 10 may comprise a wafer, as defined above, including a plurality of individual die locations thereon. The bond pads 12 are “bumped” with intermediate conductive elements 20 which project upwardly from active surface 14, or some or all of the ~~input/output~~ input/output locations for each die are redistributed using conductive traces prior to being bumped, such processes being well known in the art. If the external conductive elements (see below) are metallurgically incompatible with bond pads 12, the intermediate conductive elements 20 may be of a layer or layers of metals which will provide a better metallurgical bond therebetween. One such example, in the case of Al bond pads and tin/lead solder external conductive elements, would be to form intermediate conductive elements 20 of three superimposed layers (top to bottom) of copper, copper/chromium alloy, and chromium. It is also contemplated that the bond pads 12 may be bumped using a wire bonding capillary, or with solder of a higher melting temperature than that of another solder to be employed in external conductive elements 32, as referenced below. Intermediate conductive elements 20 may also comprise a conductive or conductor-filled epoxy, such as a silver-filled epoxy. The only significant constraints on the material and configuration selected for intermediate conductive elements 20 are compatibility with the bond pads 12 or other ~~input/output~~ input/output contacts on substrate 10 as well as with external conductive elements 32, and sufficient temperature tolerance and physical strength to withstand encapsulation of active surface 14 of substrate 10 and formation of external conductive elements 32 thereon.